

REMARKS

The Applicant thanks the Examiner for the careful examination of this application and respectfully requests the entry of the amendments indicated hereinabove.

Claims 1 - 20 are pending and rejected. Claims 1-7 are amended hereinabove.

In response to the comments in the Office Action concerning the IDS (filed September 22, 2003); a new IDS with copies of the publications and the foreign patent are submitted with this Amendment. Furthermore, in response to the Specification objection stated in the Office Action, paragraph [0033] of the Specification is amended hereinabove.

Claim 1 positively recites a memory device wherein the width of the body region is sufficient to provide a not fully depleted region. These advantageously claimed features are not taught or suggested by the patent granted to Chen et al. Chen et al. teaches away from the advantageously claimed invention because Chen et al. teaches the use of only fully-depleted devices (column 2 line 55, column 3 lines 47-48 and 50-51, column 4 lines 18-19, 25-26, and 40-42, column 5 lines 6-8, column 6 lines 12, 41 and 44).

Therefore, the Applicants respectfully traverse the Examiner's rejection of Claim 1 and respectfully assert that Claim 1 is patentable over the patent granted to Chen et al. Furthermore, Claims 2-6 are allowable for depending on allowable independent Claim 1 and, in combination, including limitations not taught or described in the reference of record.

Claim 7 positively recites a method of manufacturing a memory device wherein the width of the body region is sufficient to provide a not fully depleted region. These advantageously claimed features are not taught or suggested by the patents granted to Chen et al. or Fried et al.; either alone or in combination.

Chen et al. teaches away from the advantageously claimed invention because Chen et al. teaches the use of only fully-depleted devices (column 2 line 55, column 3 lines 47-48 and 50-51, column 4 lines 18-19, 25-26, and 40-42, column 5 lines 6-8, column 6 lines 12, 41 and 44). Fried et al. teaches away from the advantageously claimed invention because Fried et al. teaches a method of fabricating a Fin structure having a resistor formed within a thin vertically oriented semiconductor body of the Fin structure (column 2 lines 5-8, 9-14, and 30-33; column 3 lines 34-37, 43-44, and 47). Moreover, Fried et al. does not suggest a memory device wherein the width of the body region is sufficient to provide a not fully depleted region; as advantageously claimed.

Therefore, the Applicants respectfully traverse the Examiner's rejection of Claim 7 and respectfully assert that Claim 7 is patentable over the patents granted to Chen et al. and Fried et al.; either alone or in combination. Furthermore, Claims 8-16 are allowable for depending on allowable independent Claim 7 and, in combination, including limitations not taught or described in the reference of record.

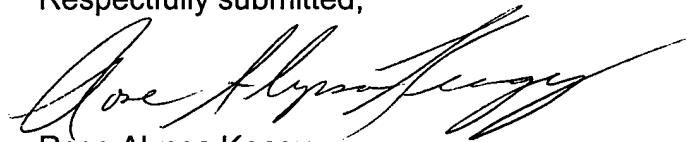
Claim 17 positively recites an integrated circuit wherein the width of the body region of the 1T DRAM device is sufficient to provide a not fully depleted region. These advantageously claimed features are not taught or suggested by the patents granted to Chen et al. or Rim; either alone or in combination.

Chen et al. teaches away from the advantageously claimed invention because Chen et al. teaches the use of only fully-depleted devices (column 2 line 55, column 3 lines 47-48 an 50-51, column 4 lines 18-19, 25-26, and 40-42, column 5 lines 6-8, column 6 lines 12, 41 and 44). Rim teaches away from the advantageously claimed invention because Rim teaches a method for fabricating FinFET devices in a tensilely strained Si on an insulator (paragraphs [0007] – [0012], [0017] and [0024]. Moreover, Rim does not suggest a memory device wherein the width of the body region is sufficient to provide a not fully depleted region; as advantageously claimed.

Therefore, the Applicants respectfully traverse the Examiner's rejection of Claim 17 and respectfully assert that Claim 17 is patentable over the patents granted to Chen et al. and Rim; either alone or in combination. Furthermore, Claims 18-20 are allowable for depending on allowable independent Claim 17 and, in combination, including limitations not taught or described in the reference of record.

For the reasons stated above, this application is believed to be in condition for allowance. Reexamination and reconsideration is requested.

Respectfully submitted,



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